

Please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please amend the Claims as follows:

1-15 (Cancelled)

16. (Withdrawn) A method of fabricating a semiconductor device, comprising the steps of:

forming wirings on a semiconductor substrate;

forming a passivation film including a first insulating film on the wirings; and

introducing an impurity into the first insulating film.

17. (Withdrawn) The method according to claim 16, further comprising the step of forming a second insulating film included in the passivation film on at least one of an upper side and a lower side of the first insulating film.

18. (Withdrawn) The method according to claim 17, wherein the second insulating film has a hygroscopicity lower than the first insulating film.

19. (Withdrawn) The method according to claim 16, wherein the second insulating film is selected the group consisting of silicon nitride film, silicon dioxide film and silicon oxynitride film.

20. (Withdrawn) The method according to claim 16, wherein the step of forming the passivation film includes the step of forming a first insulating film on the wirings using silicon oxide film materials containing over 1% carbon.

21. (Withdrawn) The method according to claim 16, wherein the step of forming a passivation film includes the step of forming a first insulating film on the wirings using an inorganic SOG (Spin-on-Glass).

22. (Withdrawn) The method according to claim 16, wherein the impurity is introduced by implantation.

23. (Withdrawn) The method according to claim 16, wherein the impurity is selected from the group consisting of argon, nitrogen and phosphorus.

24. (Withdrawn) The method according to claim 16, wherein the impurity is boron.

25. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and

5 a passivation film covering top surfaces of the interlayer insulating film and the wirings, including a first insulating film that is a modified Spin-on-Glass (SOG) film containing boron impurity and being in condition where organic component is decomposed, wherein no wiring is present on the passivation film.

26. (Previously Presented) The semiconductor device according to Claim 25, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

27. (Previously Presented) The semiconductor device according to Claim 26, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

28. (Previously Presented) The semiconductor device according to Claim 25, wherein the first insulating film contains the boron impurity to decompose organic components of an organic SOG film.

29. (Previously Presented) The semiconductor device according to Claim 28, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

30. (Previously Presented) The semiconductor device according to Claim 29, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

31. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and
a passivation film covering top surfaces of the interlayer insulating film and the wirings, including a first insulating film that is a modified Spin-on-Glass (SOG) film containing boron impurity and inorganic component, wherein no wiring is present on the passivation film.

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32. (Previously Presented) The semiconductor device according to Claim 31, wherein the passivation film includes a second insulating film, located on at least one of

an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

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33. (Previously Presented) The semiconductor device according to Claim 32, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.
